

Title (en)
THYRISTOR.

Title (de)
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Title (fr)
THYRISTOR.

Publication
EP 0486496 A1 19920527 (EN)

Application
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Abstract (en)
[origin: WO9010311A1] An MOS field effect transistor controlled thyristor is formed with a large number of mutually identical thyristor modules, each one having a base region (3) and an emitter region (4) contiguous to the base region, which between them form an emitter junction. Each module has an MOS transistor (7, 8, 9, 10), integrated with the thyristor module, for controllable shunting of the emitter junction for turn-off of the thyristor module. The MOS transistor is of depletion type and its control electrode (10) is connected, by way of a current-limiting device (R) separate for the module, to a turn-off control connection (SS) common to all the modules of the thyristor.

Abstract (fr)
Un thyristor présente une structure de thyristor produite dans un corps semi-conducteur (1). Des couches électro-isolantes (12a, 12b, 12c, 12d) sont agencées sur ledit corps semi-conducteur. Sur ces couches on a produit des éléments semi-conducteurs régulables (6a à 6d) connectés à la couche émettrice (5a à 5d) et à la couche de base (2) du thyristor. On utilise les éléments semi-conducteurs régulables pour raccourcir de manière régulée au moins une des jonctions émettrices du thyristor.

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